查询2SC5265LS供应商

Ordering number : ENN5321A

NPN Triple Diffused Planar Silicon Transistor



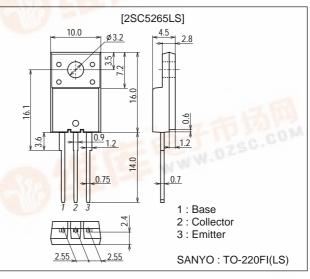
Features

- High breakdown voltage(VCBO=1200V).
- High reliability(Adoption of HVP process).
- Adoption of MBIT process.

Package Dimensions

unit : mm





Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		1200	V
Collector-to-Emitter Voltage	VCEO		600	V
Emitter-to-Base Voltage	VEBO		9	V
Collector Current	IC		4	А
Collector Current (Pulse)	ICP	190 1	8	А
Collector Dissipation	D-	7.61 9000	2	W
	PC	Tc=25°C	30	W
Junction Temperature	Tj	COM	150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector Cutoff Current	ICBO	VCB=600V, IE=0	and the second	2-1	10	μA
	ICES	V _{CE} =1200V, R _{BE} =0		2	1.0	mA
Collector-to-Emitter Sustain Voltage	VCEO(sus)	IC=100mA, IB=0	600	NAME.		V
Emitter Cutoff Current	IEBO	VEB=9V, IC=0			1.0	mA

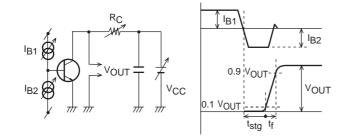
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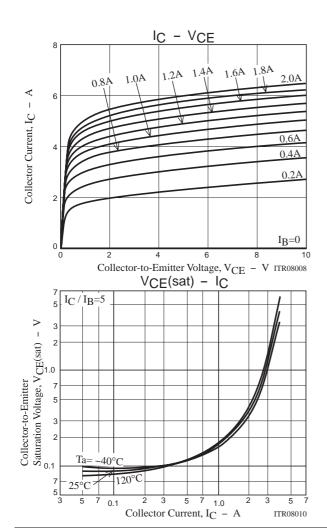
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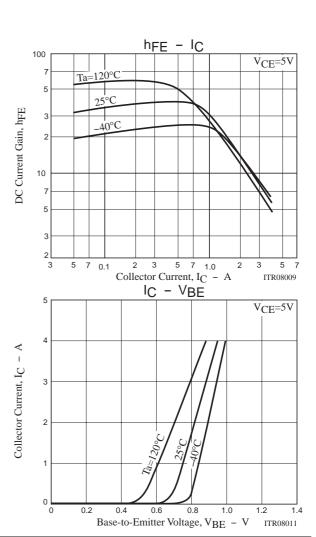
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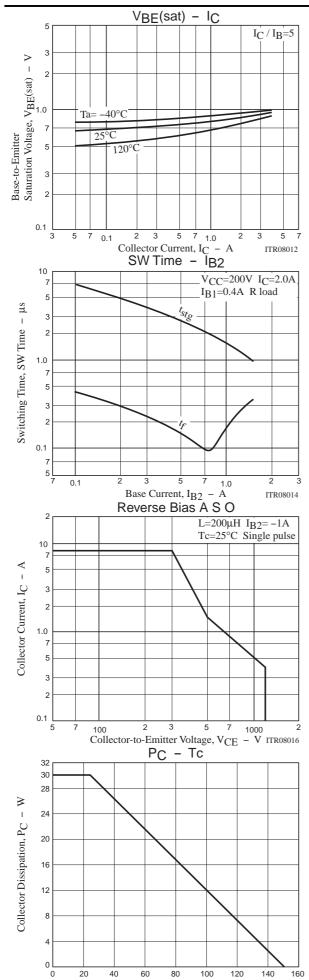
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=2.0A, IB=0.4A			1.0	V
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	IC=2.0A, IB=0.4A			1.5	V
DC Current Gain	hFE1	V _{CE} =5V, I _C =0.3A	30	40	50	
	hFE2	VCE=5V, IC=1.5A	10			
Storage Time	tstg	I _C =2.0A, I _{B1} =0.4A, I _{B2} =-0.8A			2.5	μs
Fall Time	tf	I _C =2.0A, I _{B1} =0.4A, I _{B2} =-0.8A			0.15	μs

Switching Time Test Circuit





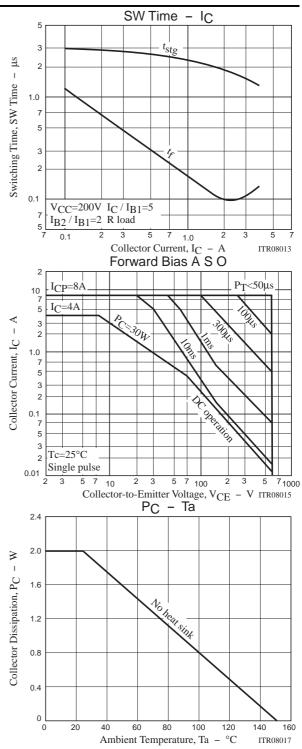




Case Temperature, Tc - °C

ITR08018

2SC5265LS



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